



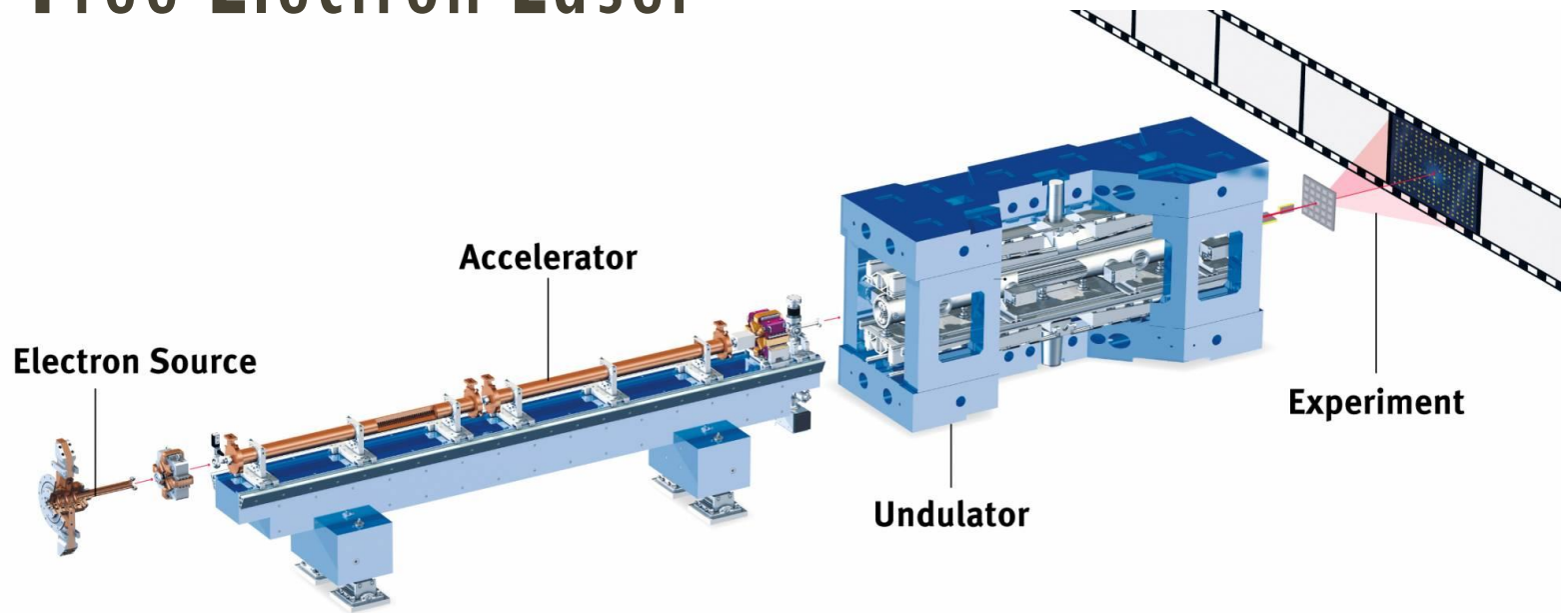
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Nano-emittance measurements in the SwissFEL

S. Borrelli, G.L. Orlandi, M. Bednarzik, C. David, E. Ferrari, V. A. Guzenko, C. Ozkan-Loch, E. Prat and R. Ischebeck

X-ray Free Electron Laser



In a XFEL it is important to generate e-beam with **low normalized emittance** and preserve it in order to produce laser pulses of the desired small wavelength.

└─ High resolution emittance measurements are necessary.

SwissFEL Nominal e-Beam Parameters

E	5.8 GeV
Q	200-10 (pC)
ϵ_N	0.4-0.2 (mm mrad)
$\sigma_{\min}$ (@10 pC)	8 μm (rms)

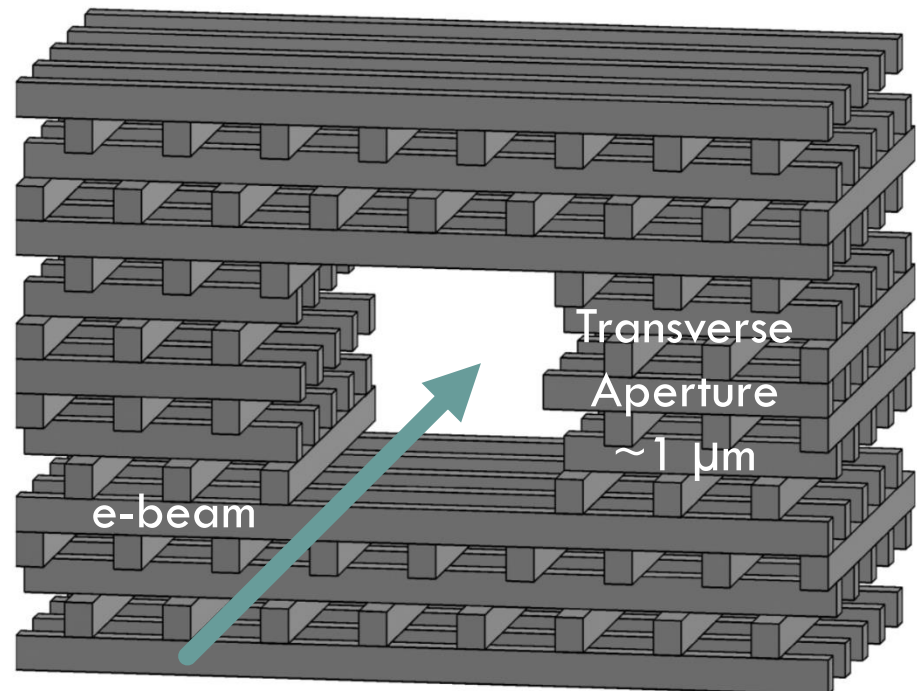
Dielectric Laser Accelerator

GORDON AND BETTY
MOORE
FOUNDATION



Compact electron accelerator in which the accelerating structure is a dielectric microstructure excited by femtosecond laser pulses.

Sub-micrometer e-beam
transverse dimensions and
low emittance are **necessary**.



Beam Transverse Profile Monitors

2-D Screens

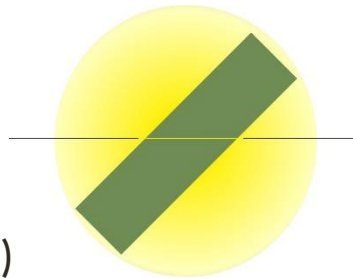
Scintillating crystal

YAG:Ce Screen

- High dynamic range but not linear
- Possible saturation
- Resolution is $8\text{ }\mu\text{m}$ (rms)

(SwissFEL)

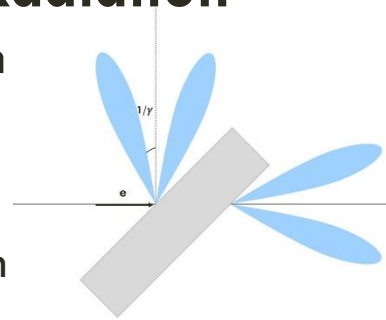
Ischebeck, R., et al. "Transverse profile imager for ultrabright electron beams." PRST-AB 18.8 (2015): 082802.



Optical Transition Radiation

OTR Screen

- Linear
- Coherent OTR emission from compressed bunch



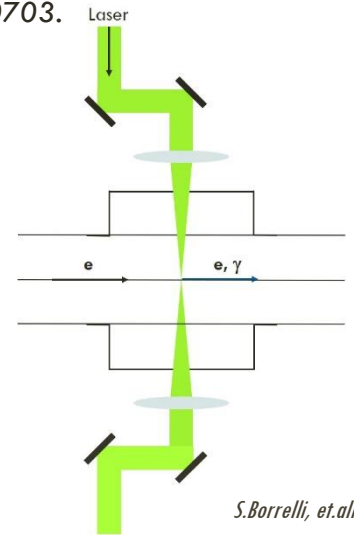
Akre, R., et al. "Commissioning the linac coherent light source injector." PRST-AB 11.3 (2008): 030703.

Laser Wire Scanners

- 1-D monitor
- Minimum laser waist limited by the laser wavelength
- Measured beam size 70 nm

(SLC-FFTB)

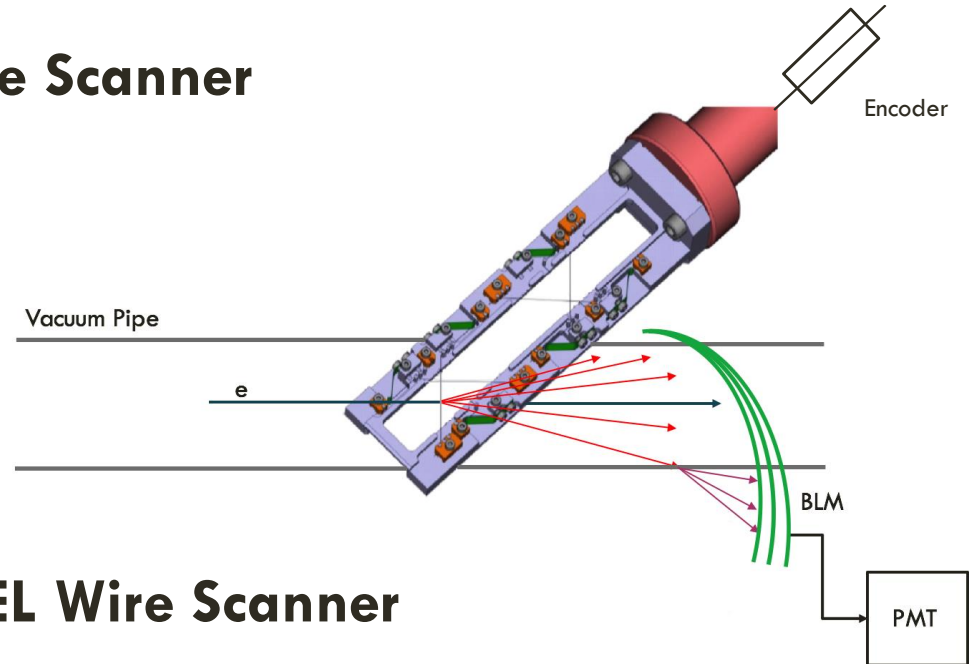
Balakin, V., et al. "Focusing of Submicron Beam for TeV-scale e^+e^- Linear Colliders." PRL 74.13 (1995): 2479.



Beam Transverse Profile Monitors

Wire Scanner

- 1-D monitor
- Multi shot measurement
- Resolution limited by
 - Wire diameter
 - Wire vibration
 - Encoder resolution
 - Beam jitter



SwissFEL Wire Scanner

- Geometrical rms resolution (5 μm W wire) 1.25 μm
- Wire vibration below the geometrical resolution
- Encoder resolution 0.1 μm

→ Reduce wire diameter to improve resolution

Orlandi, G. L., et al. "Design and experimental tests of free electron laser wire scanners." *PR-AB*, 19.9 (2016): 092802.



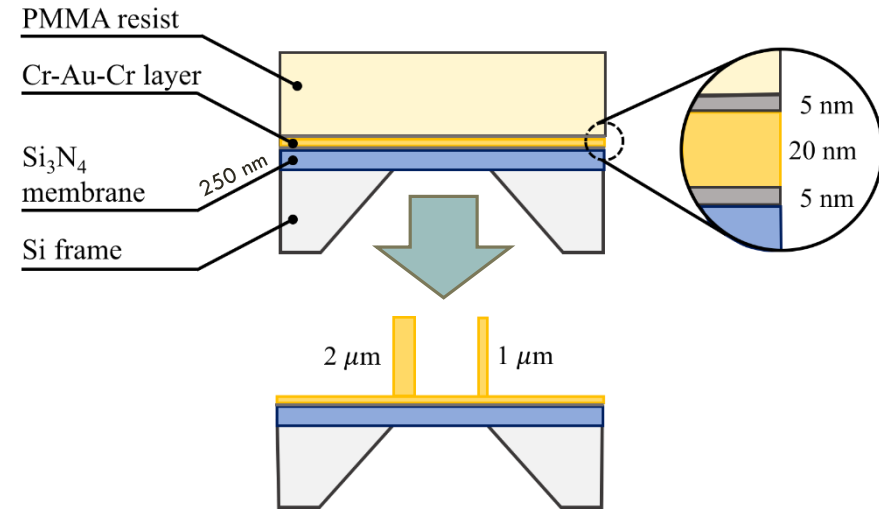
IDEA

Nanofabrication techniques to produce a 1 μm stripe on a membrane via e-beam lithography and electroplating.

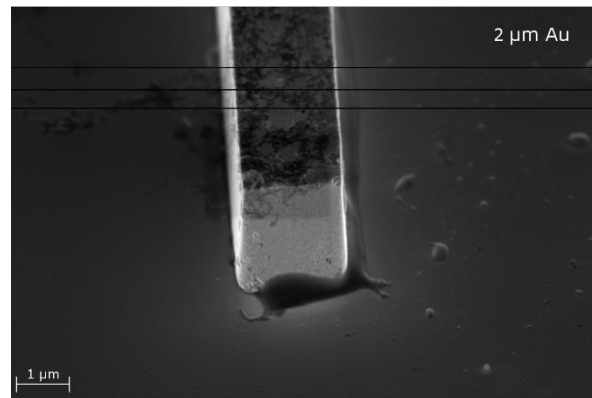
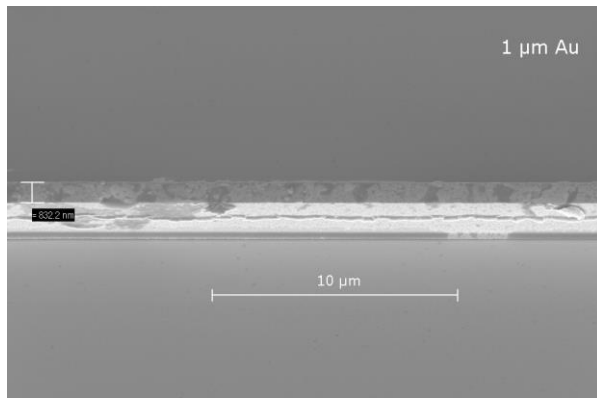
Wire Scanner on-a-chip with Sub- μm Resolution

Fabrication Technique

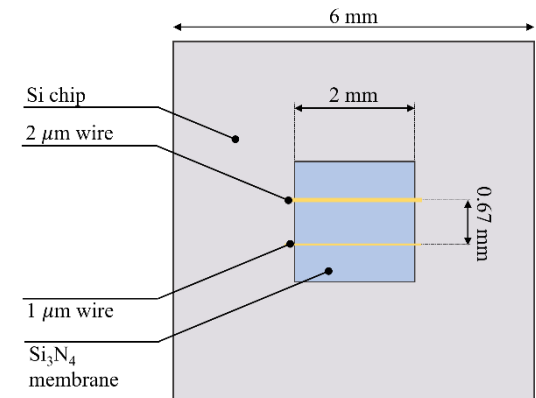
- Electron Beam Lithography on the Resist
- Resist development
- Top Cr layer removal
- Electroplating of two Au wires of different widths ($1\ \mu\text{m}$ - $2\ \mu\text{m}$)
- Resist removal



Scanning Electron Microscope characterization

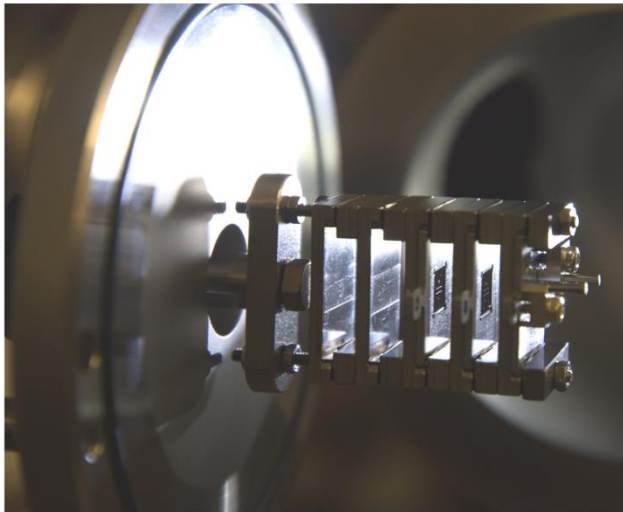
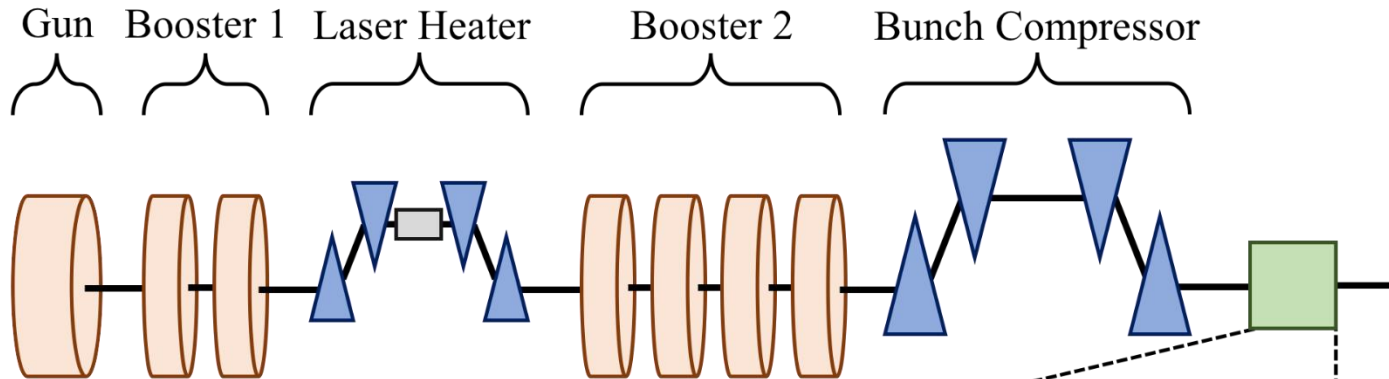


Wire Scanner on-a-chip Sketch

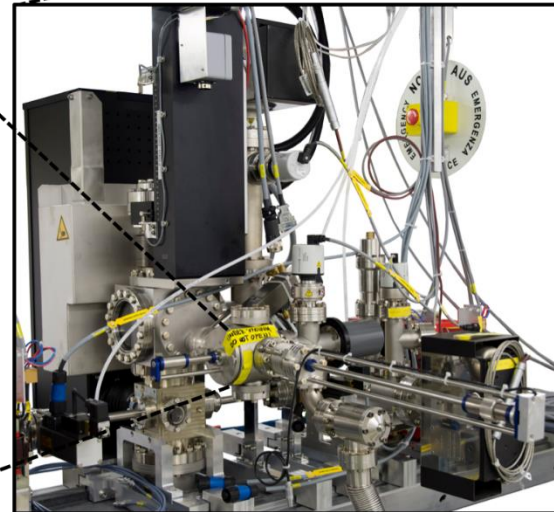


Generation & Measurement of Sub- μm e-beams

SwissFEL Injector



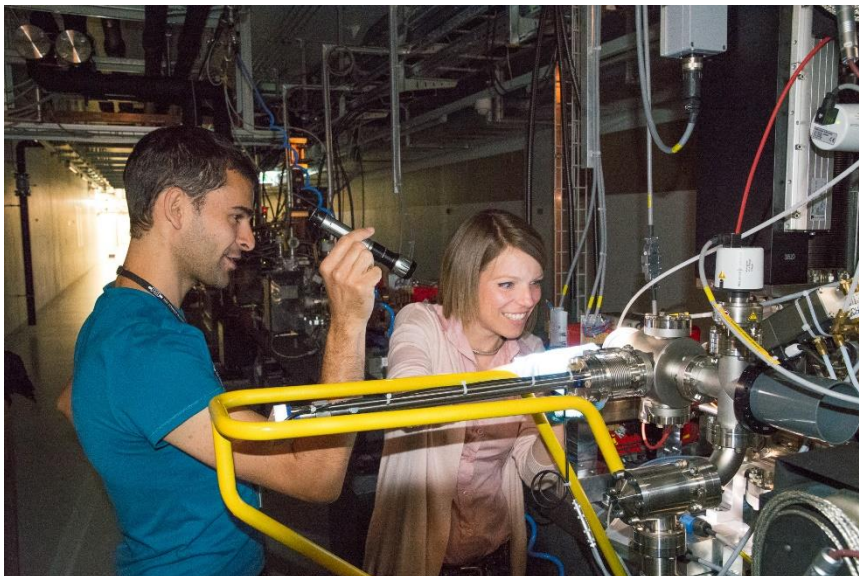
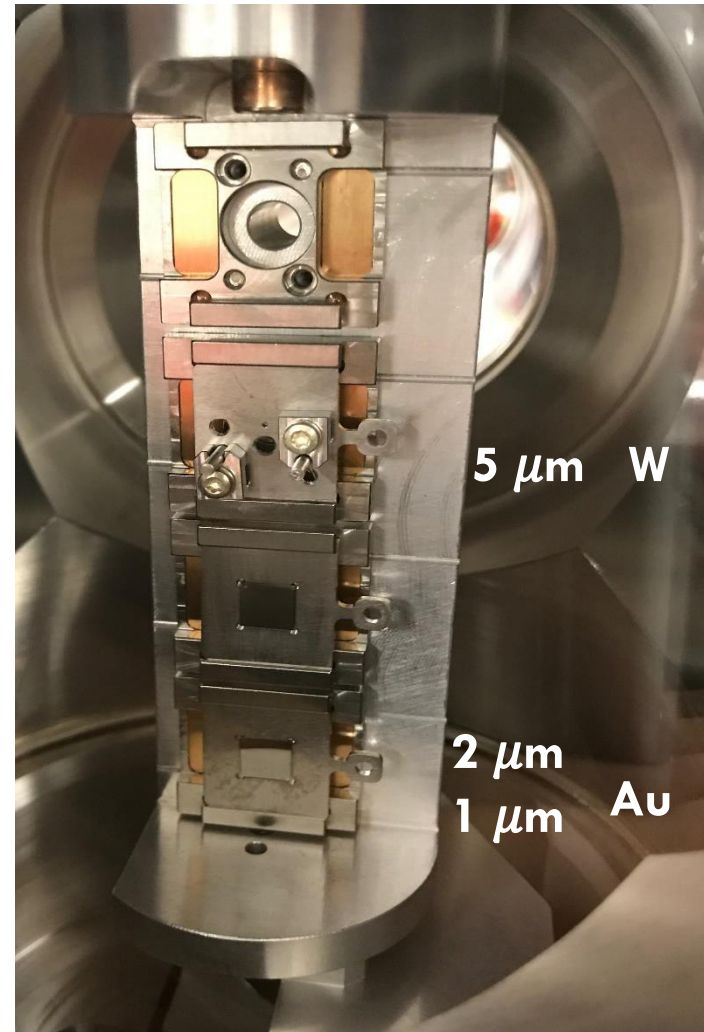
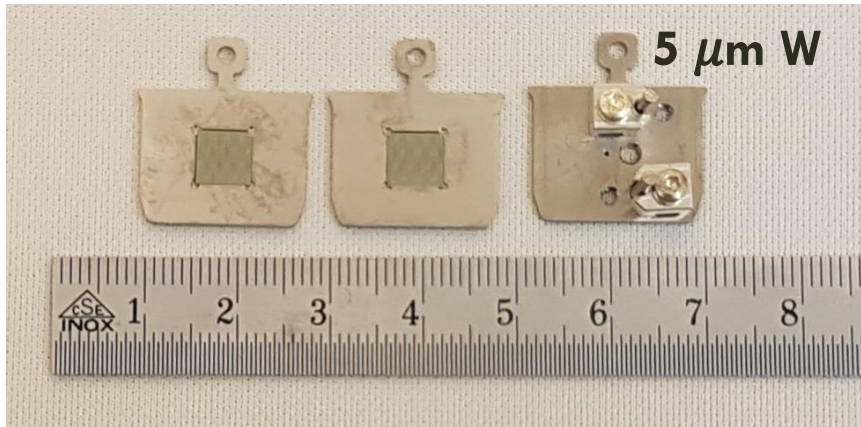
Wire Scanner



Experimental Chamber

Generation & Measurement of Sub- μm e-beams

Wire Scanners Installation



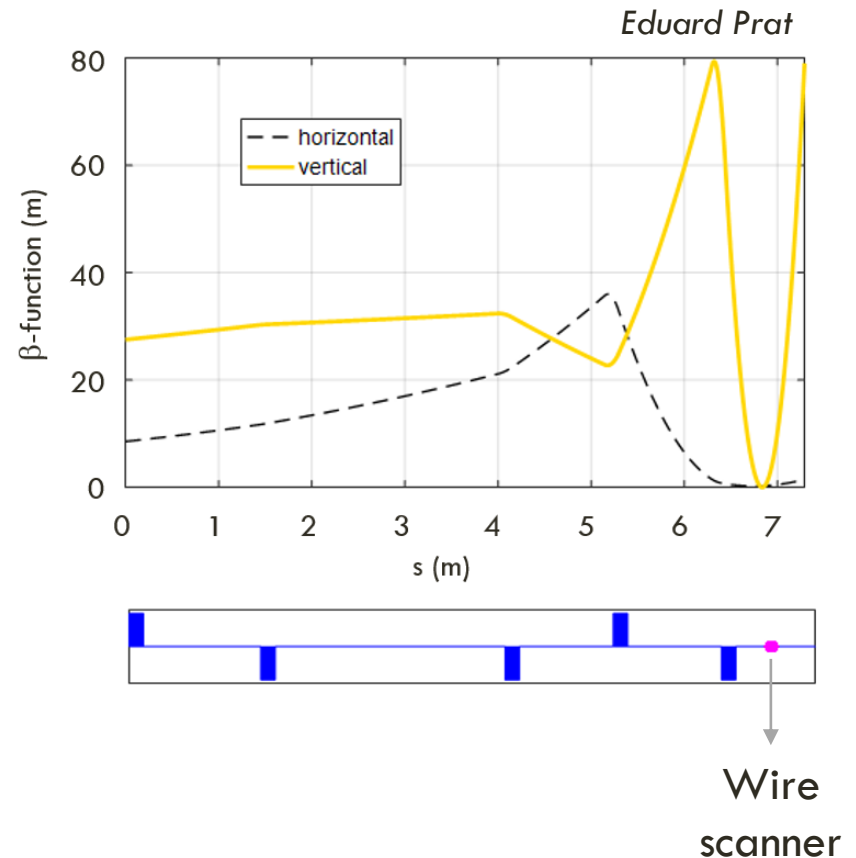
Generation & Measurement of Sub- μm e-beams

Generation of Sub- μm Relativistic e-Beams

E	330 MeV
Q	< 1 pC
$\epsilon_{N,y}$	53 nm
β_y	2.61 mm

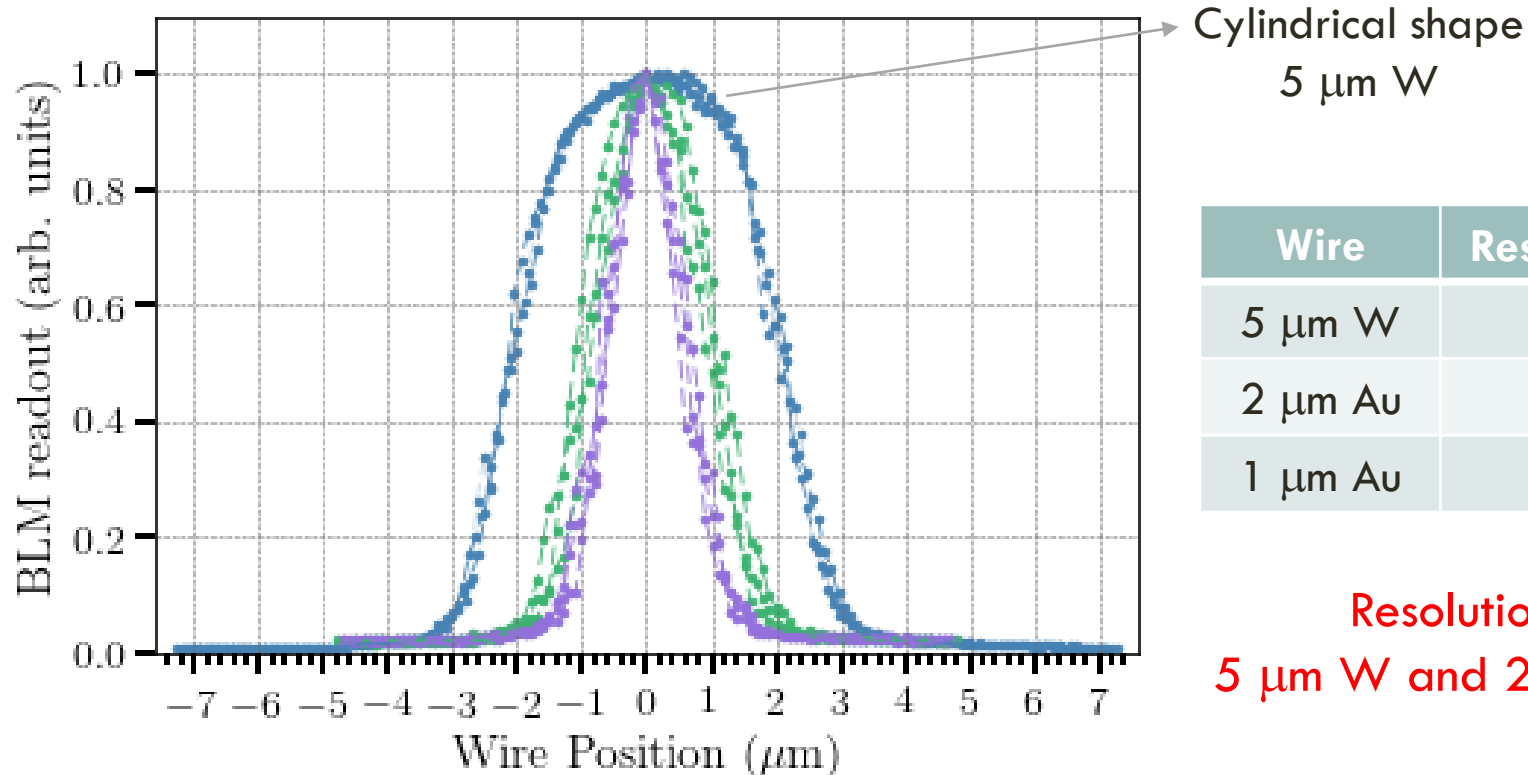
Beam Size at wire scanner location

$$\sigma_y = 463 \text{ nm (rms)}$$



Generation & Measurement of Sub- μm e-beams

Beam Profile Measurements



Wire	Resolution (μm)
5 μm W	1.25
2 μm Au	0.58
1 μm Au	0.29

Resolution limit:
5 μm W and 2 μm Au wires

— 5 μm W wire — 1 μm Au stripe
— 2 μm Au stripe

Three sequential measurements for each wire

Generation & Measurement of Sub- μm e-beams

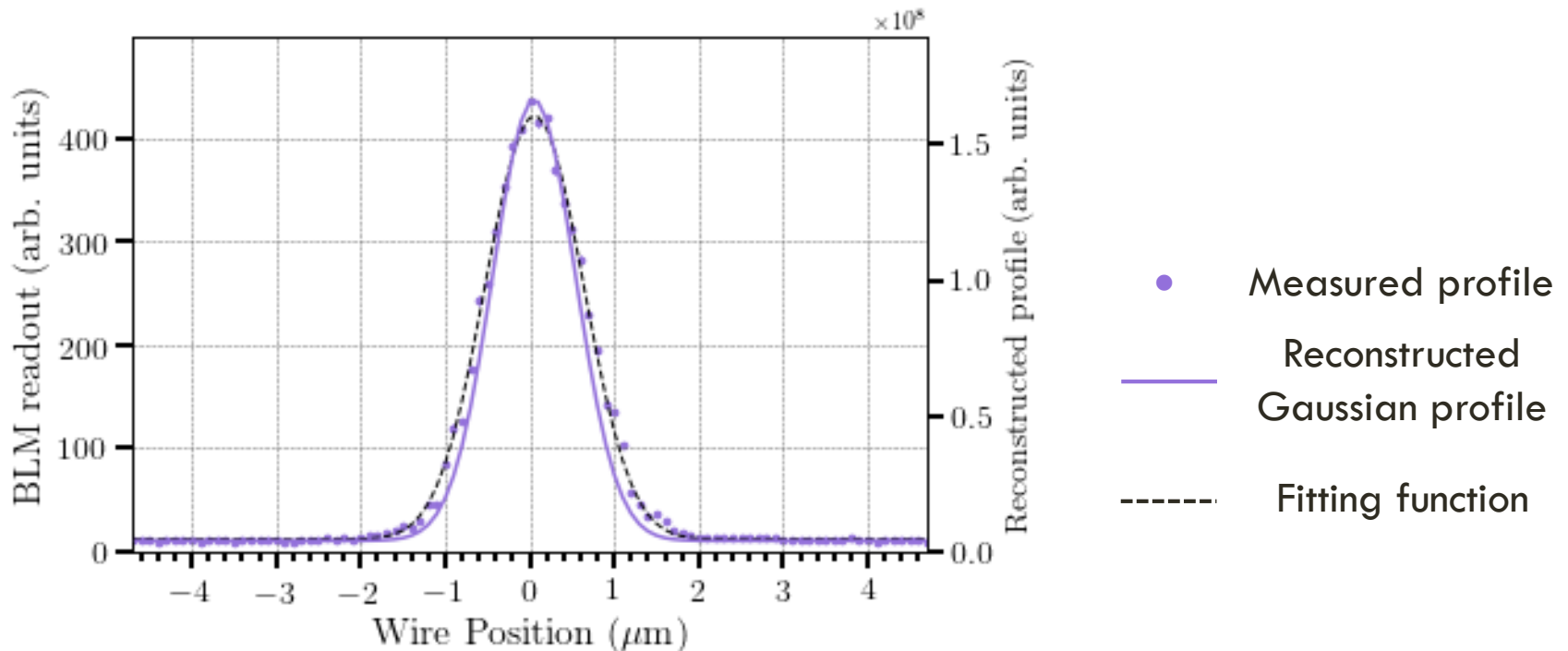
Convolution Fit

Fitting function

$$f(y; \Delta, \alpha, \sigma, \gamma) = \int t(u) \left[\Delta + \alpha e^{\frac{-(u-y-\gamma)^2}{2\sigma^2}} \right] du$$

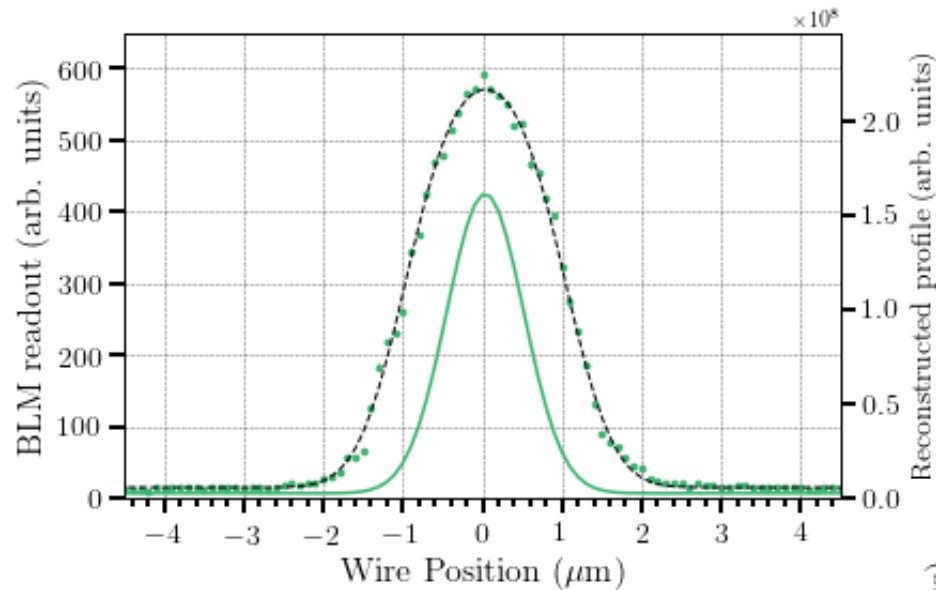
Wire shape

hyp: Gaussian Beam profile



Generation & Measurement of Sub- μm e-beams

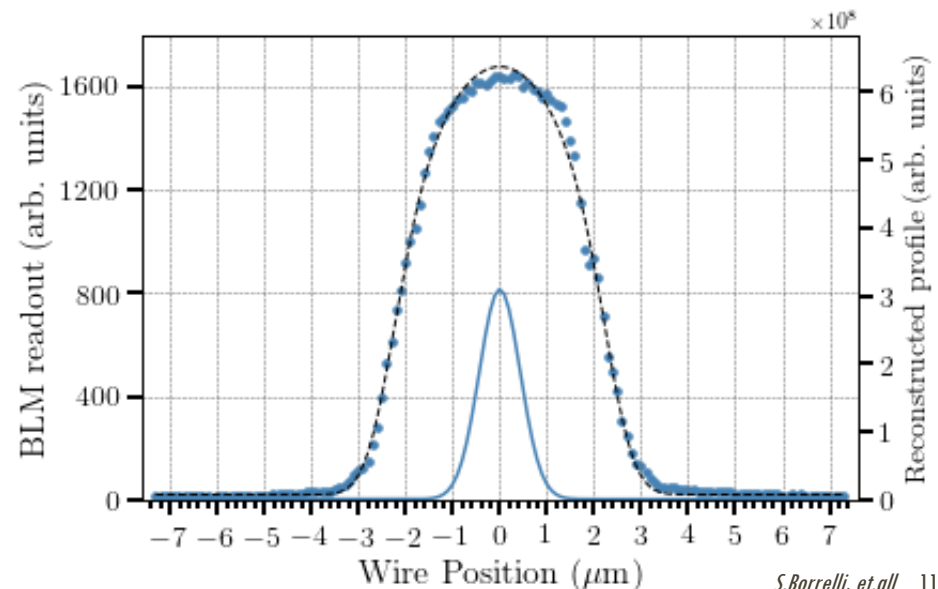
Convolution Fit



- Measured profiles
- Reconstructed
- Gaussian profiles
- Fitting function

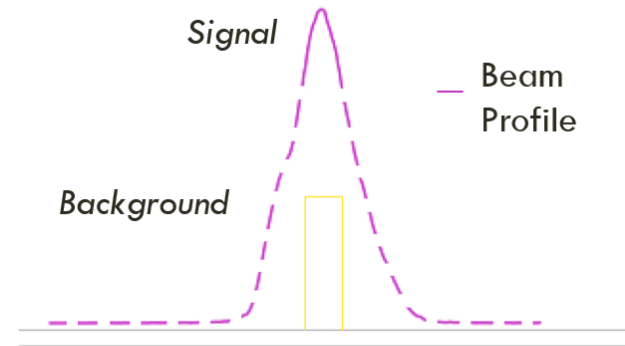
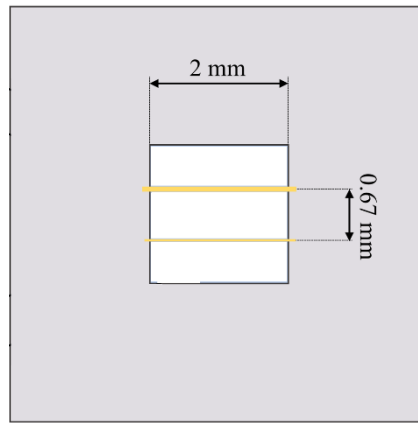
Wire	σ_y (nm)
5 μm W	462 ± 11
2 μm Au	491 ± 4
1 μm Au	491 ± 5

σ_y : Average fit sigma over 3 sequential beam profile measurement with its standard deviation



Outlook

- Membrane removal to improve the signal-to-noise ratio.



Only a small fraction of the beam traverse the membrane and the wire producing the signal of interest.

- Generate a smaller beam in the SwissFEL high energy region and test wire scanner on-a-chip prototypes with $0.3\ \mu\text{m}$ and $0.5\ \mu\text{m}$ wide stripes
- Beam jitter correction

Thanks so much!

Gian Luca Orlandi

Rasmus Ischebeck

Eduard Prat

Eugenio Ferrari

Vitaliy Guzenko

Cigdem Ozkan-Loch

Volker Schlott

Nicole Hiller

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Christian David

Martin Bednazik

Beat Rippstein

Alexandre Gobbo

Arturo Daniel Alarcon



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BACKUP SLIDES

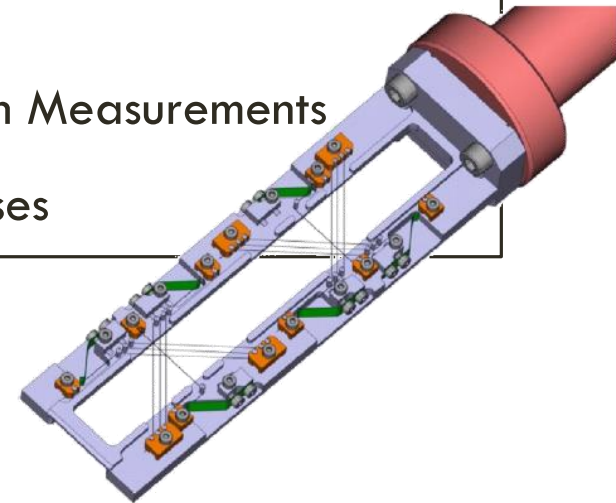
SwissFEL WIRE SCANNER

SwissFEL Wire Scanners (WSCs) consist of a wire fork equipped with two couples of wires:

- 5 μm W wires
- 12.5 μm Al(99):Si(1) wires

High Resolution Measurements

Low Beam Losses



Fork inserted in the vacuum by means of an Ultra-High Vacuum linear-stage driven by a two phase stepper motor.

Fork inserted at 45° w.r.t. the vertical direction so that for each couple, **one wire scans** the beam **vertically** and the **other horizontally**.

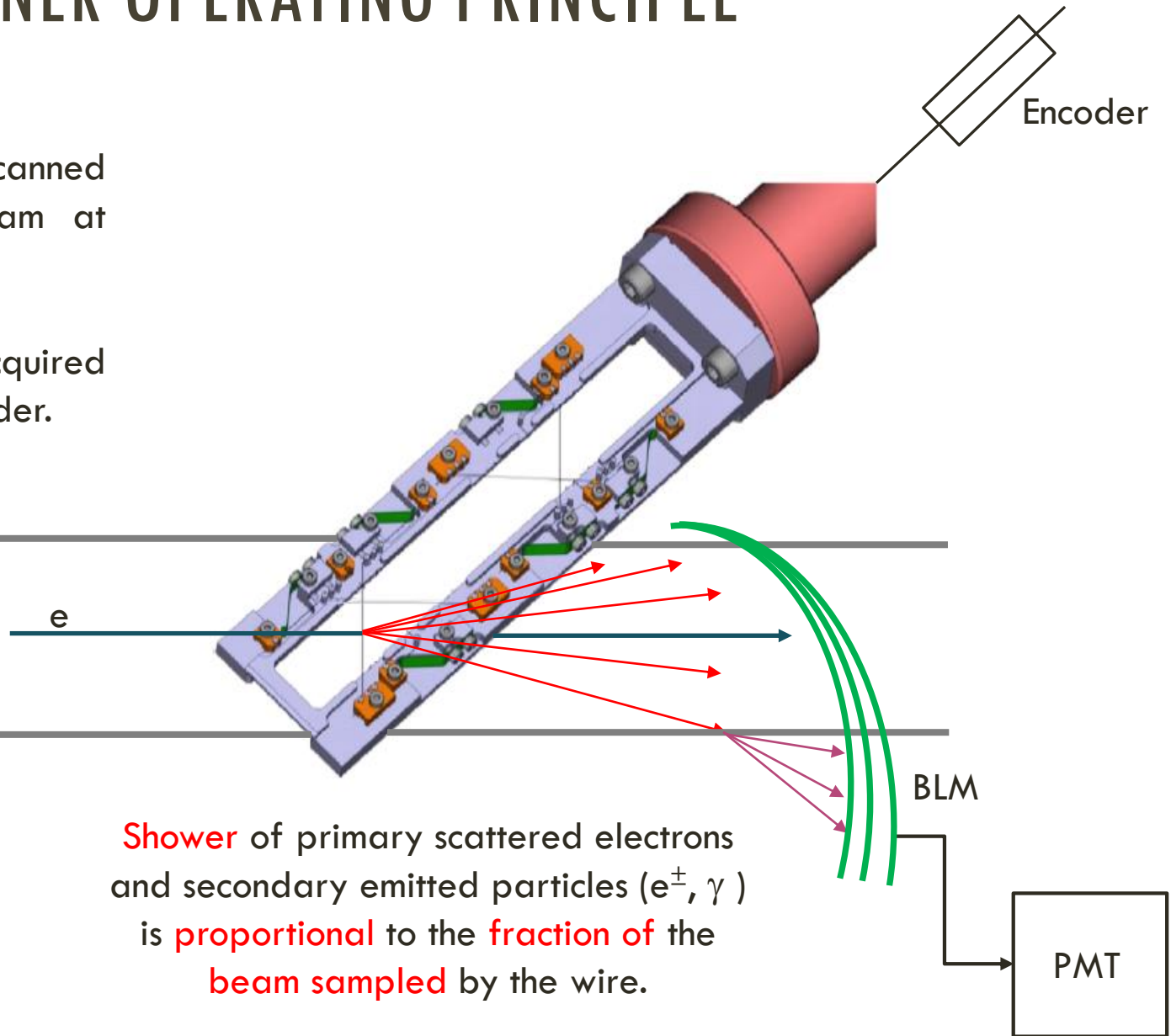


WIRE SCANNER OPERATING PRINCIPLE

A wire is scanned through the beam at constant velocity.

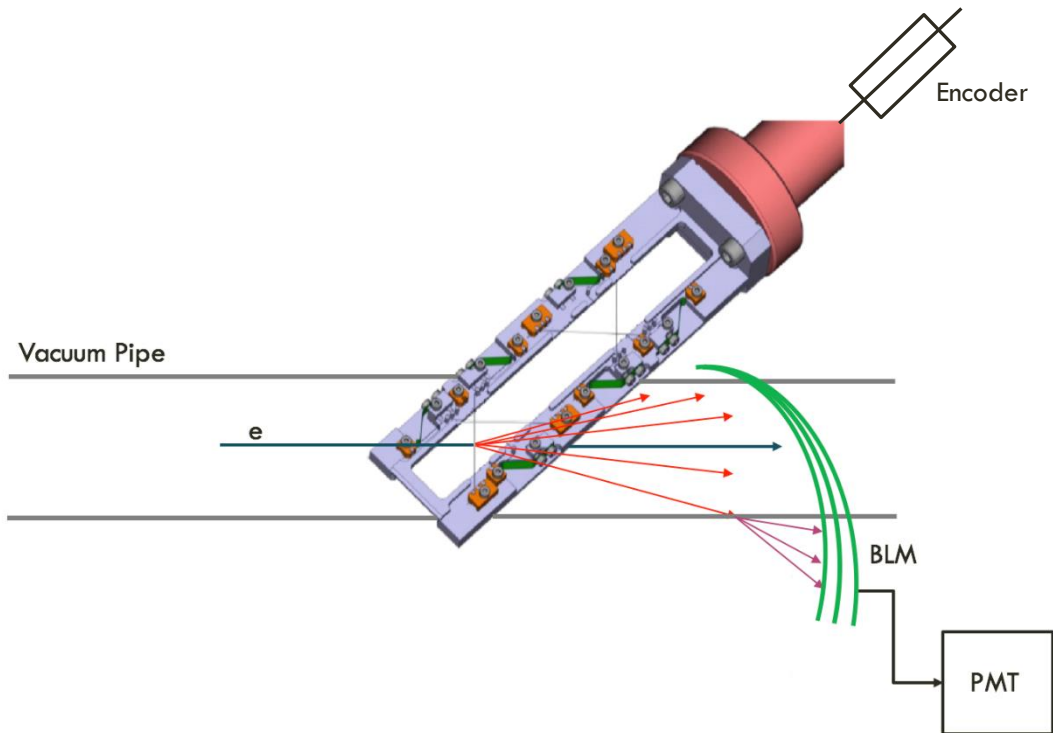
Wire position acquired by a linear encoder.

Vacuum Pipe



Shower of primary scattered electrons and secondary emitted particles ($e^{\pm}, \gamma$) is **proportional** to the **fraction of the beam sampled** by the wire.

WIRE SCANNER OPERATING PRINCIPLE

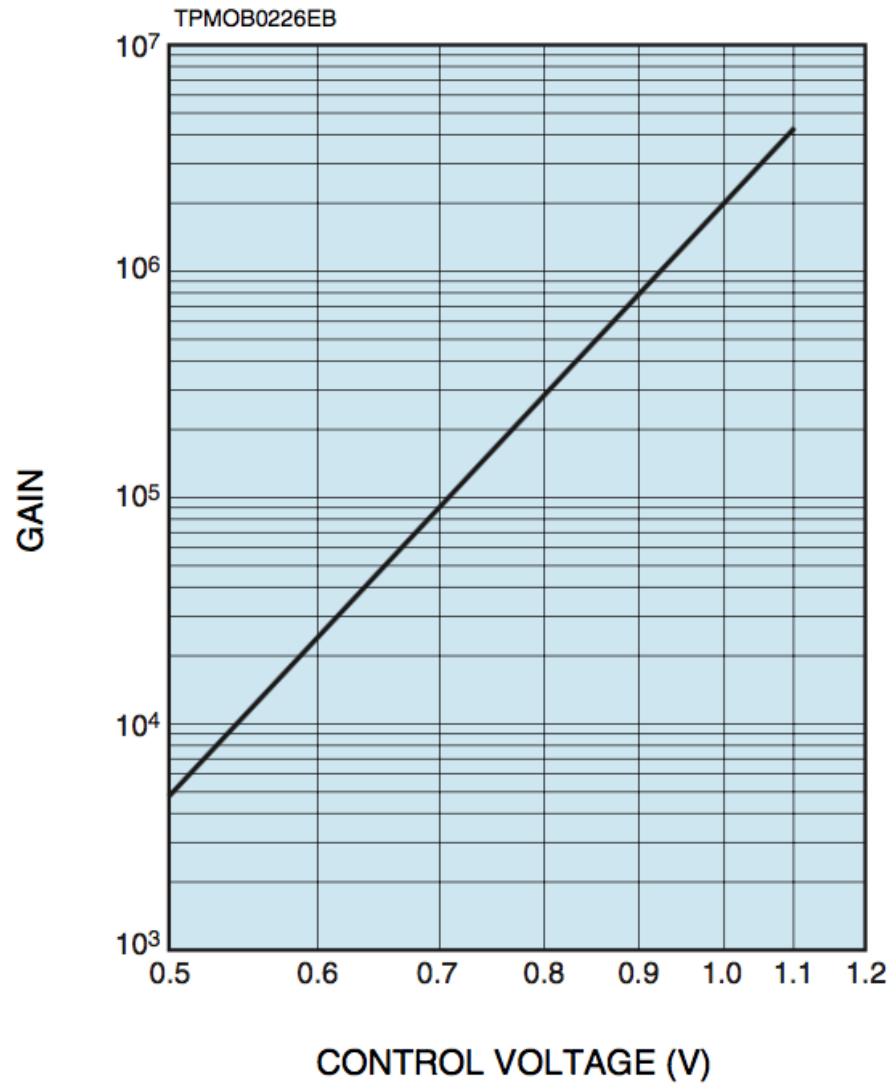


Out-of-vacuum detection of the shower's forward component through scintillator fiber.

Scintillator light sent to a PMT with an adjustable gain in the range $[5 \cdot 10^3, 4 \cdot 10^6]$.

The **beam's** horizontal / vertical **profile** can be **reconstructed** acquiring in **beam synchronous** way the **wire position** and **BLM signal**.

BLM GAIN CURVE



SUB-MICROMETER RESOLUTION WIRE SCANNER

WIRE HEATING BY E-BEAM EXPOSURE

Rough estimation

**Energy transferred
by the beam
particles to the
wire material**

$$E_{loss} = \frac{dE}{dt} * t * \rho_{Au} * \underbrace{Ne * R}_{\text{N}^\circ \text{ of particles intercepted by the wire}}$$

Collisional stopping power in
Au for $E = 320 \text{ MeV}$

$$\frac{dE}{dt} = 1.5 \text{ MeV cm}^2/\text{g}$$

N° of particles
intercepted by the wire

$$E_{loss} = 5.3 * 10^{-11} \text{ J}$$

SUB-MICROMETER RESOLUTION WIRE SCANNER

WIRE HEATING BY E-BEAM EXPOSURE

Rough estimation

**Increase of
temperature**

$$\Delta T = \frac{E_{loss}}{c_s * m_{eff}}$$

Gold specific heat

Wire effective mass

$$m_{eff} = \rho_{Au} * \sigma_b * t * \frac{w}{\sqrt{12}}$$

For each RF-shot

$$\Delta T = 14 \text{ K}$$

Wire Scanner on-a-chip with Sub- μm Resolution

STRIPE HEATING BY E-BEAM EXPOSURE

2 μm Au stripe

Irradiated power

$$P_{irr} = \sigma A T^4 \epsilon$$

Area of stripe involved

$$A = (3.2 \mu\text{m} * 2 \mu\text{m}) * 4$$

Gold emissivity

$$\epsilon = 0.47$$

$$T = 300 \text{ K} + \Delta T = 314 \text{ K}$$

$$P_{irr} = 1.106 * 10^{-9} \text{ W}$$

Wire Scanner on-a-chip with Sub- μm Resolution

STRIPE HEATING BY E-BEAM EXPOSURE

2 μm Au stripe

Absorbed power

$$P_{in} = E * 10 \text{ Hz} = 5.3 * 10^{-10} \text{ W}$$

Absorbed energy

$$\Delta P = 1.106 * 10^{-9} \text{ W} > P_{in}$$

SUB-MICROMETER RESOLUTION WIRE SCANNER

WIRE HEATING BY E-BEAM EXPOSURE

12.5 μm Al & 5 μm W wires comparison

Rough estimation

	ΔT (°C)	Melting Point (°C)
GOLD	3.7	1064
ALUMINUM	0.7	660
TUNGSTEN	3.7	3695

BACKGROUND FROM THE MEMBRANE

Beam Parameters

E_e	=	320 MeV
Q_b	=	1 pC
$\sigma_{x/y}$	=	3.2 μm

Wire & membrane parameters

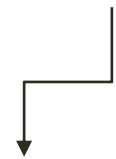
Wire Width	w_{Au}	=	2 μm
Wire Thickness	t_{Au}	=	2 μm
Membrane Thickness	$t_{Si_3N_4}$	=	0.250 μm

**Radiative energy
loss of the beam
intercepted by the
wire in the
 $Si_3N_4 + Au$ thickness**

$$\Delta E \Big|_{rad}^{Si_3N_4+Au} = \frac{E_e}{L_R^{Si_3N_4+Au}} * t_{Si_3N_4+Au} * \Delta N_e$$



$Si_3N_4 + Au$
radiation length
 $L_R^{Si_3N_4+Au} = 0.3 \text{ cm}$



Fraction of e^-
intercepted by the
wire.

BACKGROUND FROM THE MEMBRANE

**Radiative energy
loss of remaining
part of the beam in
 Si_3N_4 thickness**

$$\Delta E \Big|_{rad}^{Si_3N_4} = \frac{E_e}{L_R^{Si_3N_4}} * t_{Si_3N_4} * (N_e - \Delta N_e)$$

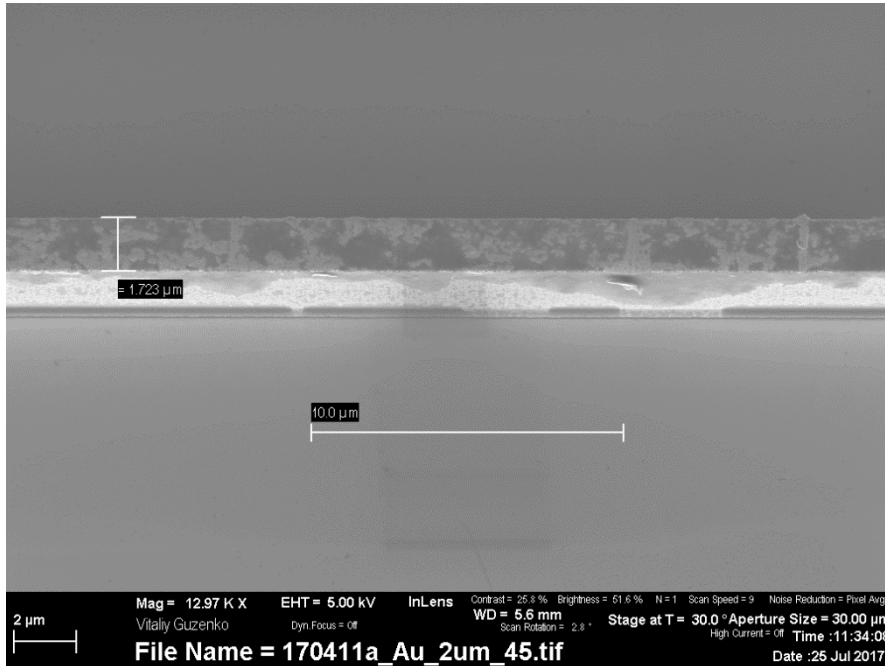
Si_3N_4
radiation length
 $L_R^{Si_3N_4+Au} = 8.3 \text{ cm}$

Fraction of e^-
passing only the
membrane

**Background to signal
ratio**

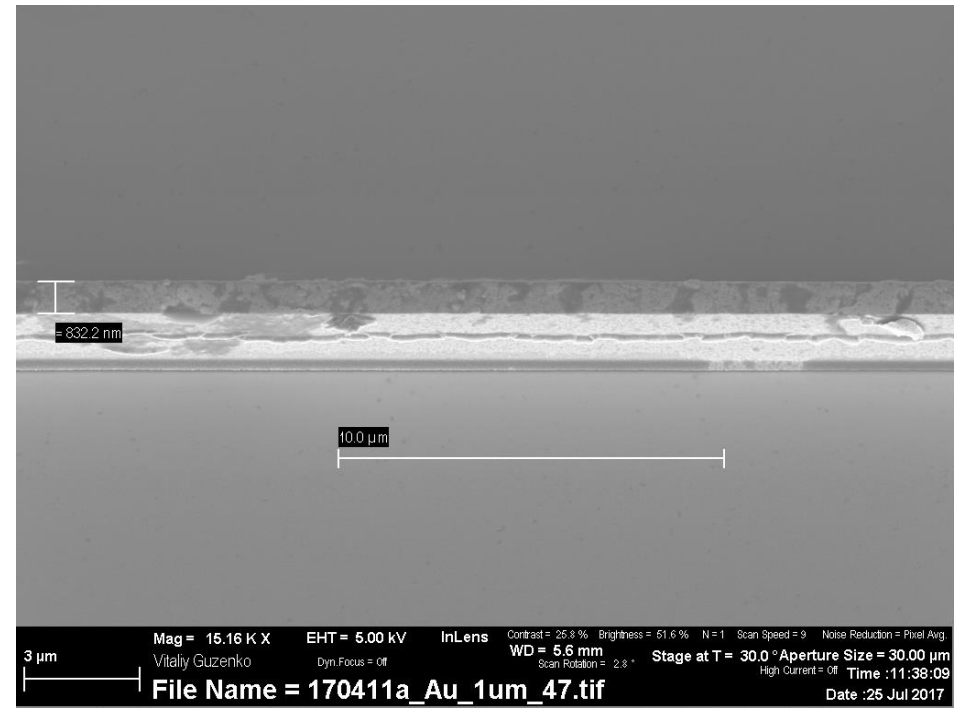
$$\frac{\Delta E \Big|_{rad}^{Si_3N_4}}{\Delta E \Big|_{rad}^{Si_3N_4+Au}} = 18$$

WIRES AFTER THE BEAM EXPOSURE



2 μm Au wire

$$\sigma_w = 0.6 \mu\text{m}$$



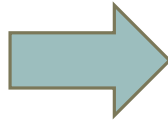
1 μm Au wire

$$\sigma_w = 0.3 \mu\text{m}$$

NICKEL WIRES

Beam losses estimation

$$\text{Beam loss} \propto Z^2$$



$$\frac{Au}{Ni} = 8$$

8 times
lower signal

Background from the membrane

Background to
signal ratio

$$\frac{\Delta E|_{rad}^{Si_3N_4}}{\Delta E|_{rad}^{Si_3N_4+Ni}} = 9$$



SKETCHES

SwissFEL

Design parameters		
Design parameters for the electron beam	Operation Mode	
	Long Pulses	Short Pulses
Charge per bunch (pC)	200	10
Core slice emittance (mm.mrad)	0.43	0.18
Projected emittance (mm.mrad)	0.65	0.25
Slice energy spread (keV, rms)	350	250
Relative energy spread (%)	0.006	0.004
Peak current at undulator (kA)	2.7	0.7
Bunch length (fs, rms)	25	6
Bunch compression factor	125	240

Performance of Aramis		
Performance of Aramis for 5.8 GeV electron energy and 1Å lasing wavelength	Long Pulses	short Pulses
Maximum saturation length (m)	47	50
Saturation pulse energy (μJ)	150(*)	3
Effective saturation power (GW)	2.8	0.6
Photon pulse length at 1 Å (fs, rms)	21	2.1
Number of photons at 1 Å (×10e9)	73	1.7
Bandwidth, rms (%)	0.05	0.04
Peak brightness (# photons.mm-2.mrad-2.s-1/0.1% bandwidth)	7.e32	1.e32
Average Brightness (# photons.mm-2.mrad-2.s-1/0.1% bandwidth)	2.3e21	5.7e18

SwissFEL

Performance of Athos (SASE)	
Performance of Athos (SASE), for example at 3.4 GeV electron energy and 2.8 nm lasing wavelength	Long Pulses
Maximum saturation length (m)	22 m
Saturation pulse energy (μJ)	360
Effective saturation power (GW)	11.2
Photon pulse length at 2.8 nm (fs, rms)	13
Number of photons at 2.8 nm ($\times 10^9$)	5000
Bandwidth (%)	0.19
Peak brightness (# photons.mm ⁻² .mrad ⁻² .s ⁻¹ /0.1% bandwidth)	6.e35
Average Brightness (# photons.mm ⁻² .mrad ⁻² .s ⁻¹ /0.1% bandwidth)	8.e23

